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Zhengqing John Qi
Jed Rankin
Eisuke Narita
Masayuki Kagawac

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Zhengqing John Qi,^a Jed Rankin,^b Eisuke Narita,^c and Masayuki Kagawac^c

^aGLOBALFOUNDRIES Inc., 275 Fuller Road, Albany, New York 12203, United States

^bGLOBALFOUNDRIES Inc., 1000 River Street, Essex Junction, Vermont 05452, United States

^cToppan Photomask Inc., 1000 River Street, Essex Junction, Vermont 05452, United States

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